

SHORT BIO

Dr. Stanislav Tyaginov received his PhD degree in physics at the post-graduate school of the Ioffe Physical-Technical Institute in 2006. Starting from 2008 he has been working at the Technical University of Vienna where he led the physics-based hot-carrier degradation model development group. For the period of 2018-2020 he was a Marie Curie postdoctoral fellow at *imec*, where he is currently employed as a principal researcher. Dr. Tyaginov has been serving as a technical program committee member at the IIRW (2020 general chair), IRPS, ESREF, IPFA, EDTM and has authored/co-authored more than 150 publications in peer reviewed scientific journals as well as in conference proceedings. Among them, more than 60 are journal papers. His scientific interests include HCD, BTI, TDDB, self-heating in Si, SiGe/Ge, 2D channel material based and SiC devices, as well as tunneling phenomena.